

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI6969BDQ-T1-E3

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Si6969BDQ

Vishay Siliconix

Dual P-Channel 1.8-V (G-S) MOSFET

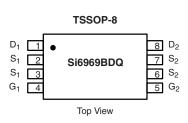
| PRODUCT SUMMARY | | | | |
|---------------------|------------------------------------|--------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | | |
| - 12 | 0.030 at V _{GS} = - 4.5 V | - 4.6 | | |
| | 0.040 at V _{GS} = - 2.5 V | - 3.8 | | |
| | 0.055 at V _{GS} = - 1.8 V | - 3.0 | | |

FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFETs

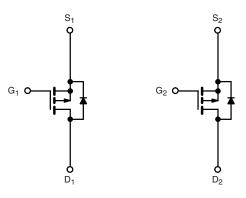


RoHS*



Ordering Information: Si6969BDQ-T1

Si6969BDQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | | | |
|--|------------------------|-----------------------------------|-------------|--------------|------|--|
| Parameter | | Symbol | 10 s | Steady State | Unit | |
| Drain-Source Voltage | | V _{DS} | - 12 | | V | |
| Gate-Source Voltage | | V _{GS} | ± 8 | | | |
| Continuous Dusin Coursent /T 150 °C\2 | T _A = 25 °C | - I _D | - 4.6 | - 4.0 | | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 70 °C | | - 3.8 | - 3.2 | | |
| Pulsed Drain Current (10 µs Pulse Width) | | I _{DM} | - 30 | | А | |
| Continuous Source Current (Diode Conduction) ^a | | I _S | - 1.0 | - 0.7 | | |
| Mariana Bara Birata di a | T _A = 25 °C | P _D | 1.14 | 0.83 | W | |
| Maximum Power Dissipation ^a | T _A = 70 °C | | 0.73 | 0.53 | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|---------------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Marrian de Angliant | t ≤ 10 s | - R _{thJA} | 88 | 110 | °C/W |
| Maximum Junction-to-Ambient ^a | Steady State | | 120 | 150 | |
| Maximum Junction-to-Foot (Drain) | Steady State | R _{thJF} | 65 | 80 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

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Datasheet of SI6969BDQ-T1-E3 - MOSFET 2P-CH 12V 4A 8TSSOP

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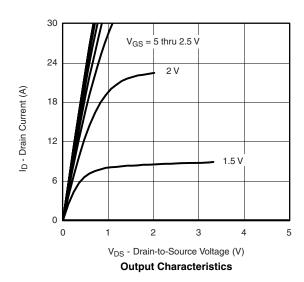
| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | |
|--|---------------------|---|--------|--------|-------|----|--|
| Parameter | Symbol | Test Conditions Min. Typ. | | Max. | Unit | | |
| Static | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ | - 0.45 | | - 0.8 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 8 V$ | | | ± 100 | nA | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = - 9.6 V, V _{GS} = 0 V | | | - 1 | | |
| | | $V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$ | | | - 25 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} - 8 V, V _{GS} = - 4.5 V | - 30 | | | Α | |
| | | $V_{GS} = -4.5 \text{ V}, I_D = -4.6 \text{ A}$ | | 0.024 | 0.030 | Ω | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = -2.5 \text{ V}, I_D = -3.8 \text{ A}$ | | 0.031 | 0.040 | | |
| | | V _{GS} = - 1.8 V, I _D = - 3.0 A | | 0.044 | 0.055 | | |
| Forward Transconductance ^a | 9 _{fs} | $V_{DS} = -8 \text{ V}, I_{D} = -4.6 \text{ A}$ | | 18 | | S | |
| Diode Forward Voltage ^a | V_{SD} | $I_S = -1.25 \text{ A}, V_{GS} = 0 \text{ V}$ | | - 0.68 | - 1.1 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Qg | | | 16.5 | 25 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.6 \text{ A}$ | | 2 | | nC | |
| Gate-Drain Charge | Q _{gd} | | | 4.7 | | 1 | |
| Turn-On Delay Time | t _{d(on)} | | | 20 | 40 | | |
| Rise Time | t _r | V_{DD} = - 6 V, R_L = 6 Ω | | 35 | 60 | | |
| Turn-Off Delay Time | t _{d(off)} | $\text{I}_\text{D}\cong\text{-}$ 1.0 A, $\text{V}_\text{GEN}=\text{-}$ 4.5 V, $\text{R}_\text{G}=\text{6}~\Omega$ | | 110 | 180 | ns | |
| Fall Time | t _f | | | 90 | 150 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = - 1.25 A, dI/dt = 100 A/μs | | 100 | 200 | | |

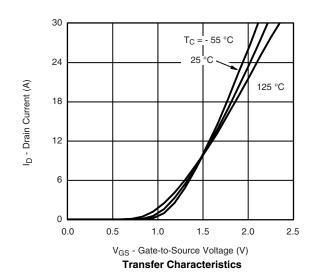
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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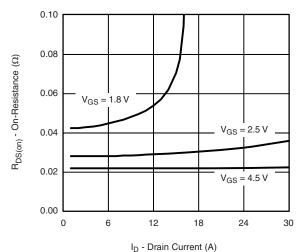
V_{GS} - Gate-to-Source Voltage (V)

Is - Source Current (A)

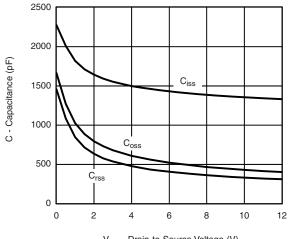
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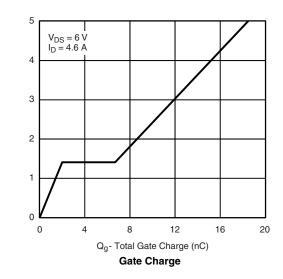


On-Resistance vs. Drain Current

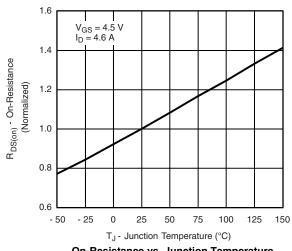


 V_{DS} - Drain-to-Source Voltage (V)

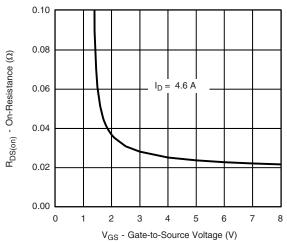




30 $T_J = 150 \, ^{\circ}C$ 10 T_J = 25 °C 0.0 V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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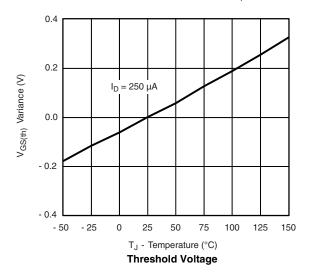


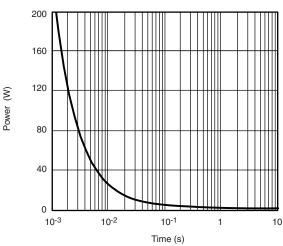
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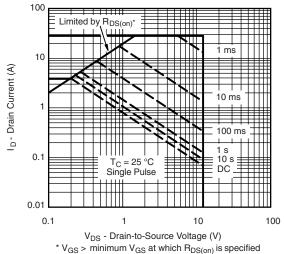
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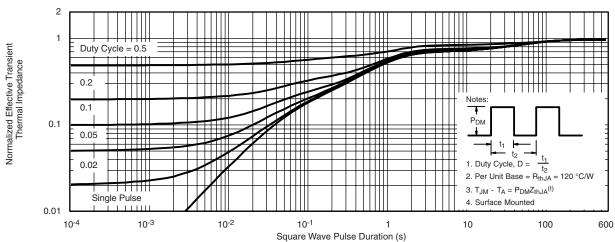




Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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Datasheet of SI6969BDQ-T1-E3 - MOSFET 2P-CH 12V 4A 8TSSOP

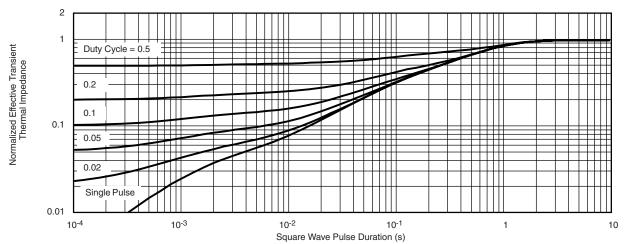
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see https://www.vishay.com/ppg?72017.

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Datasheet of SI6969BDQ-T1-E3 - MOSFET 2P-CH 12V 4A 8TSSOP

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